

Silicon PNP Power Transistors

2SA1758

DESCRIPTION

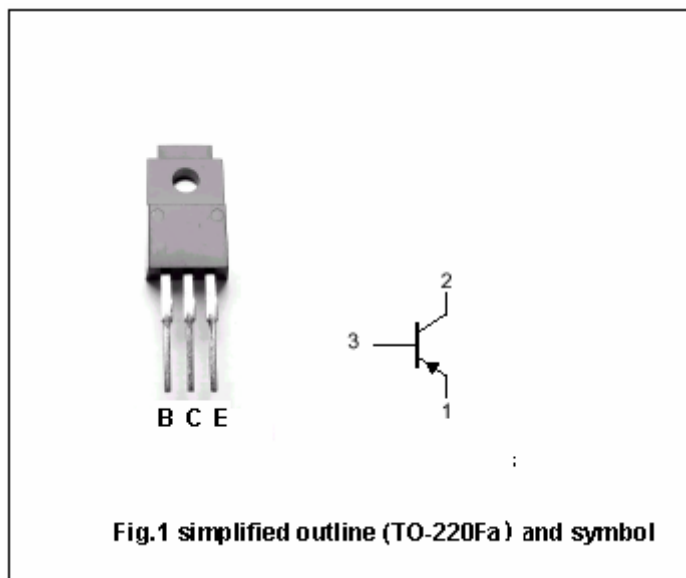
- With TO-220Fa package
- Low collector saturation voltage
- Wide area of safe operation

APPLICATIONS

- For power switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-12	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	30	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA, I _B =0	-60			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-50 μ A, I _C =0	-5			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-6A; I _B =-0.3A			-0.3	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-8A; I _B =-0.4A			-0.5	V
V _{BEsat-1}	Base-emitter saturation voltage	I _C =-6A; I _B =-0.3A			-1.2	V
V _{BEsat-2}	Base-emitter saturation voltage	I _C =-8A; I _B =-0.4A			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-10	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μ A
h _{FE}	DC current gain	I _C =-2A; V _{CE} =-2V	60		320	
f _T	Transition frequency	I _C =-1A; V _{CE} =-10V		90		MHz

◆ h_{FE} Classifications

D	E	F
60-120	100-200	160-320

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PACKAGE OUTLINE

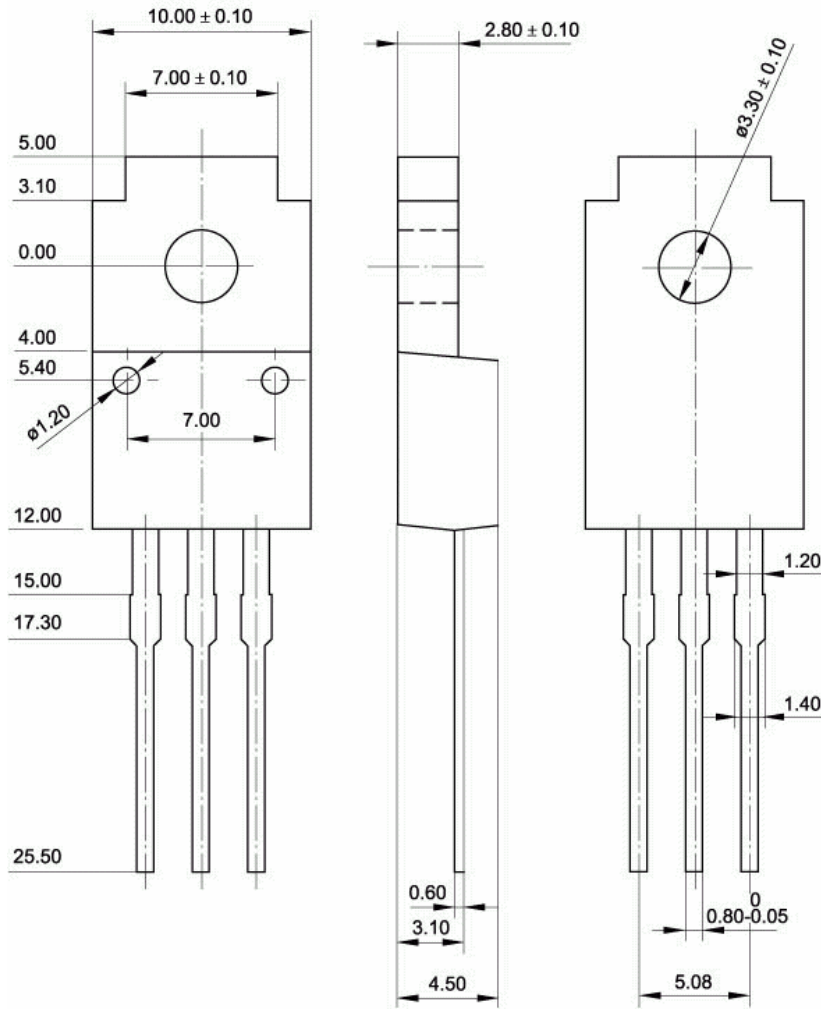


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)